



Contribution ID: 239

Type: Poster Presentation

Effect of annealing temperature and time on α -hematite thin films prepared via dip coating method for photoelectrochemical water splitting applications

In this study, four layers of hematite (α -Fe₂O₃) thin films were prepared layer-by-layer on fluorine-doped tin oxide (FTO) using the dip coating method at withdrawal speed of 60 mm/min, annealed at 400-700°C for 2 hours, 30 minutes each layer. Following similar procedure additional samples were prepared and annealed at 700°C but different time intervals of 5, 10 and 20 minutes for each of the four layers. The prepared α -Fe₂O₃ thin films were used as photoanodes in a three-electrode photoelectrochemical (PEC) system for water splitting. X-ray diffraction (XRD) and Raman spectroscopy studies confirmed the preparation of highly crystalline hematite thin films of good purity. The α -Fe₂O₃ films showed good optical absorption in the visible region because of their bandgap which was estimated to be 2.06-2.10 eV. The highest photocurrent density of 60 μ A/cm² at 1.5 V vs reversible hydrogen electrode (RHE) was obtained for films annealed at 700°C for 30 mins for each layer. Electrochemical Impedance Spectroscopy (EIS) showed the reduced charge transfer resistance and increased capacitance of the α -Fe₂O₃ photoanodes annealed at 700°C for 30 mins for each layer, which has been related to improved photocurrent density obtained for the films. This study affirmed that the annealing of α -Fe₂O₃ films at higher temperatures and for prolonged time can enhanced their PEC properties for water splitting.

Keywords: Hematite photoanode, dip coating, water splitting, annealing temperature, annealing time

Apply to be considered for a student ; award (Yes / No)?

Yes

Level for award;(Hons, MSc, PhD, N/A)?

MSc

Primary author: Ms MSIZA, Nombuso (university of pretoria)

Presenter: Ms MSIZA, Nombuso (university of pretoria)

Session Classification: Poster Session

Track Classification: Track F - Applied Physics